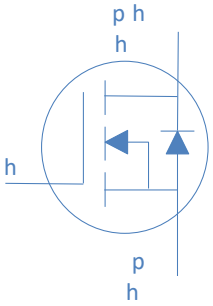
65V N-Ch Power MOSFET

p
h p h h h
h hh
P
H P
p p

h h
p P hh h h
p h h h hp h
h H ph

V_{DS}		65	V
$R_{DS(on),typ}$	V_{GS}=10V	2.7	m
$R_{DS(on),typ}$	V_{GS}=4.5V	3.7	m
I_D		82	A



Part Number	Package	Marking
HGA028NE6AL	TO-220F	GA028NE6AL

Absolute Maximum Ratings at T_j=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current	I_D	T_C=25℃	82	A
		T_C=100℃	58	
Drain to Source Voltage	V_{DS}	-	65	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	400	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.1mH, T_C=25℃	80	mJ
Power Dissipation	P_D	T_C=25℃	41	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	R_{JA}	65	℃/W
Thermal Resistance Junction-Case	R_{JC}	3.65	℃/W

Electrical Characteristics at T_j=25℃ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 A	65	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250 A	1.0	1.6	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=60V, T_j=25℃	-	-	1	A
		V_{GS}=0V, V_{DS}=60V, T_j=100℃	-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	2.7	3.2	m
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=20A	-	3.7	4.6	m
Transconductance	g_{fs}	V_{DS}=5V, I_D=20A	-	70	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz	-	1.30	-	

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=30V, f=1MHz	-	4021	-	pF
Output Capacitance	C_{oss}		-	1625	-	
Reverse Transfer Capacitance	C_{rss}		-	90	-	
Total Gate Charge	Q_g(10V)	V_{DD}=30V, I_D=20A, V_{GS}=10V	-	68	-	nC
Total Gate Charge	Q_g(4.5V)		-	34	-	
Gate to Source Charge	Q_{gs}		-	8	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	14	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=30V, I_D=20A, V_{GS}=10V, R_G=10 ,	-	14	-	ns
Rise time	t_r		-	13	-	
Turn off Delay Time	$t_{d(off)}$		-	49	-	
Fall Time	t_f		-	19	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=30V, I_F=20A, dI_F/dt=100A/ s	-	50	-	ns
Reverse Recovery Charge	Q_{rr}		-	45	-	nC

Fig 1. Typical Output Characteristics

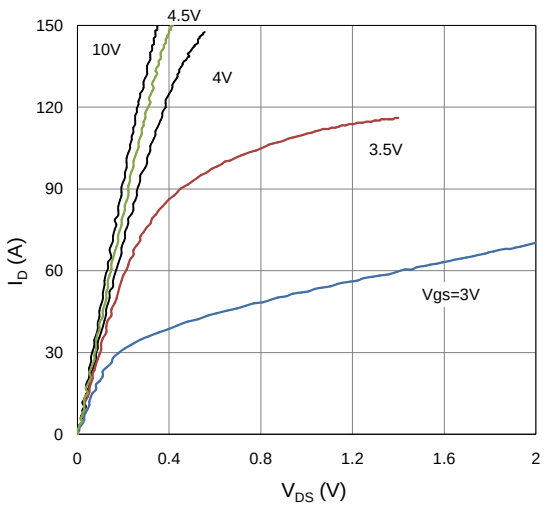


Figure 2. On-Resistance vs. Gate-Source Voltage

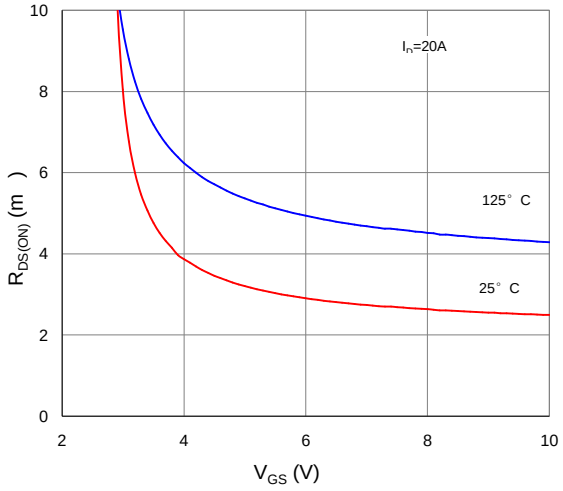


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

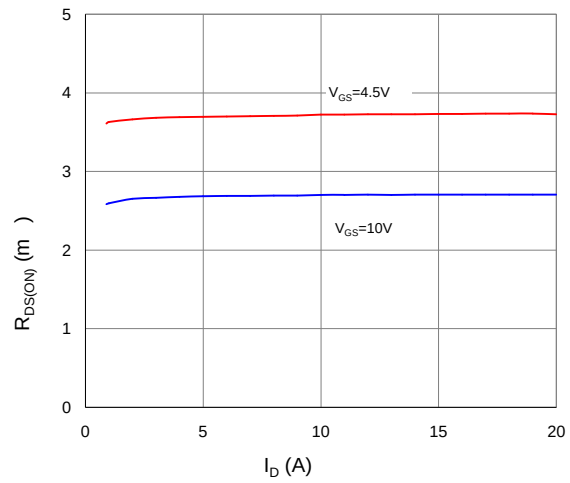


Figure 4. Normalized On-Resistance vs. Junction Temperature

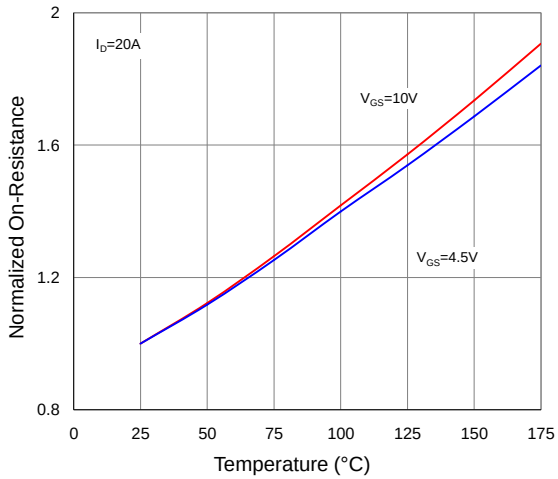


Figure 5. Typical Transfer Characteristics

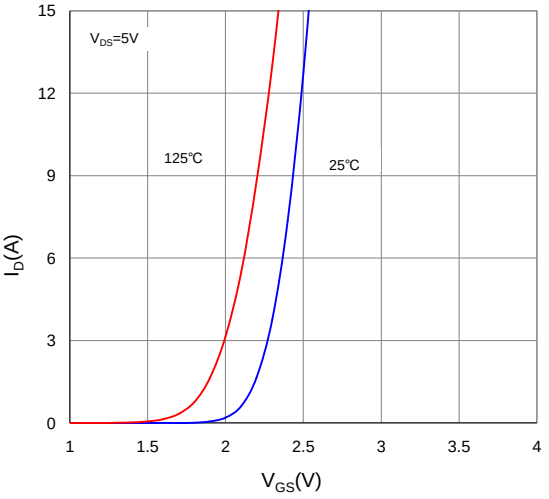


Figure 6. Typical Source-Drain Diode Forward Voltage

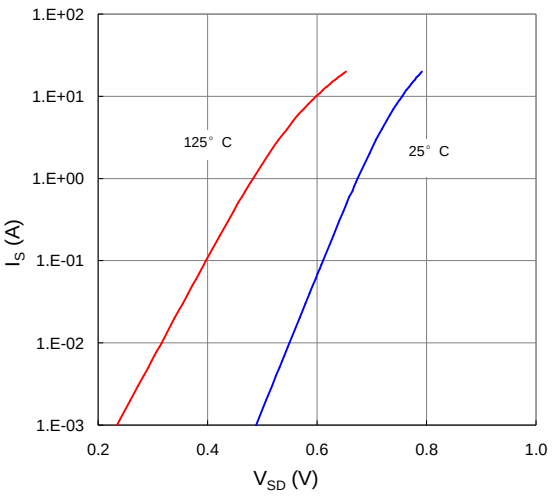


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

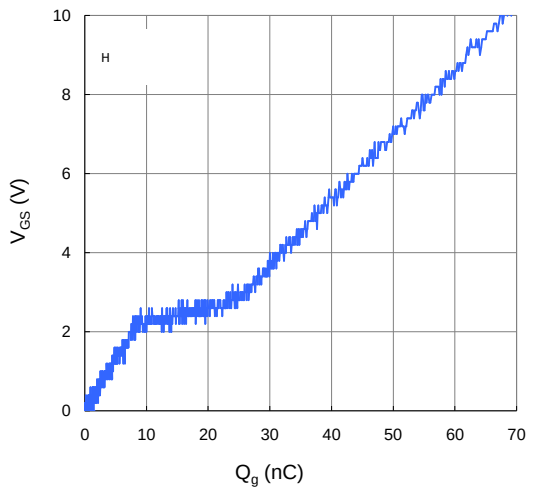


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

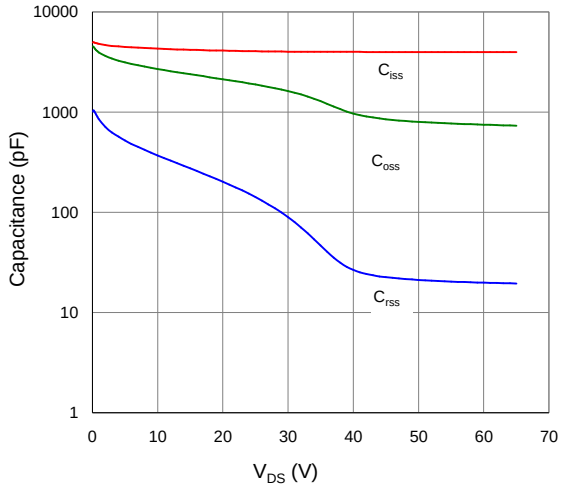


Figure 9. Maximum Safe Operating Area

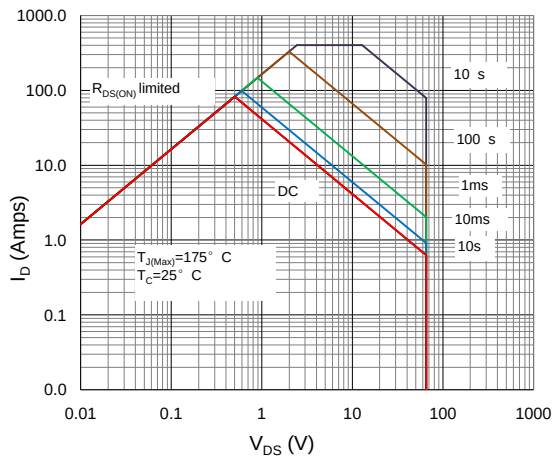


Figure 10. Maximun Drain Current vs. Case Temperature

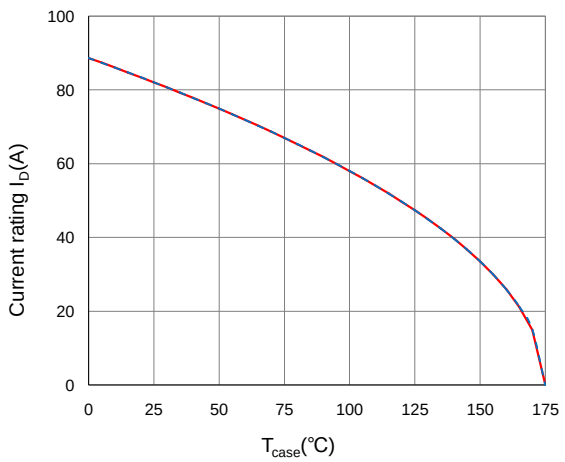
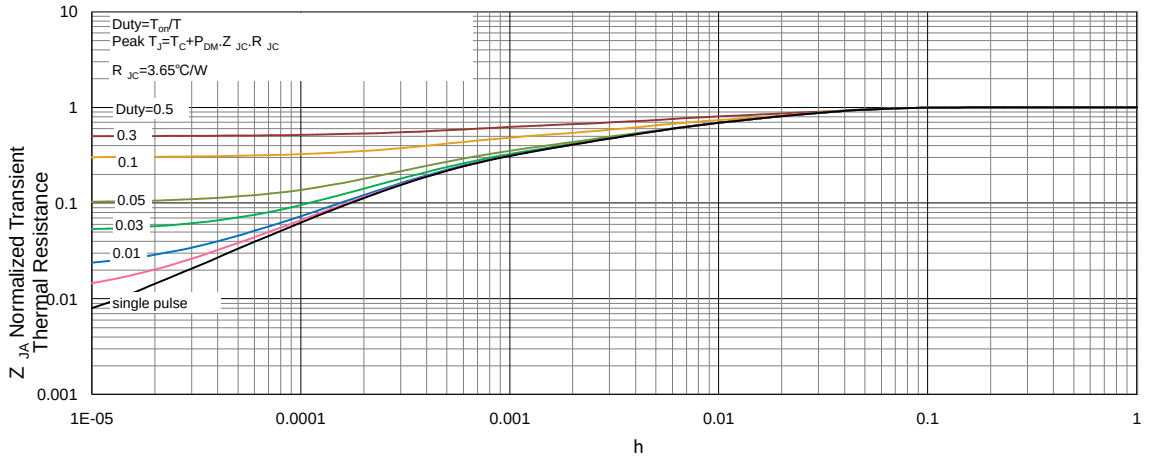
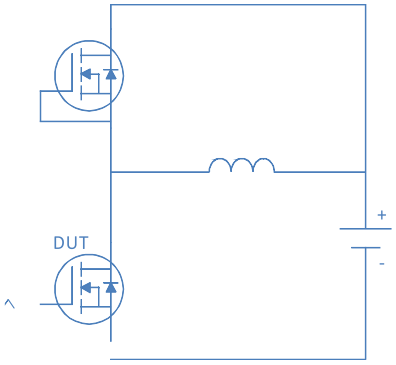
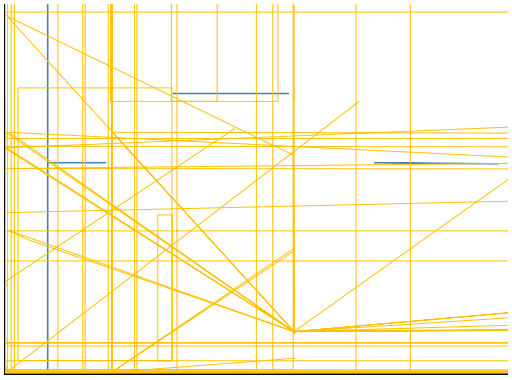


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

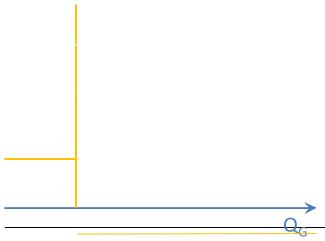


Inductive switching Test

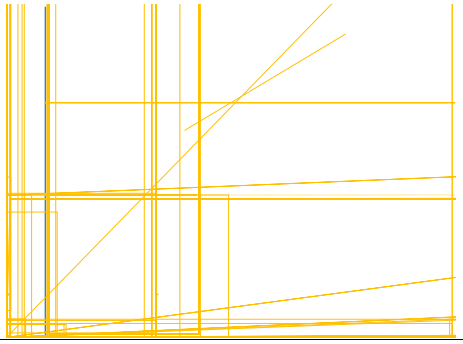




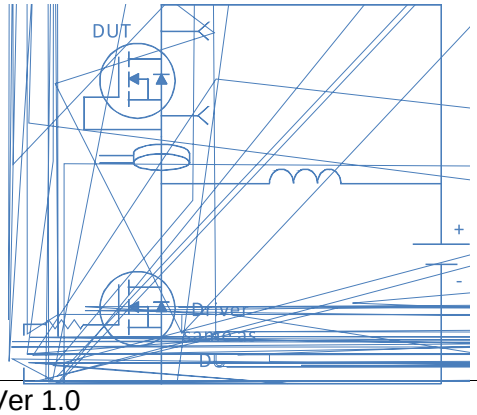
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

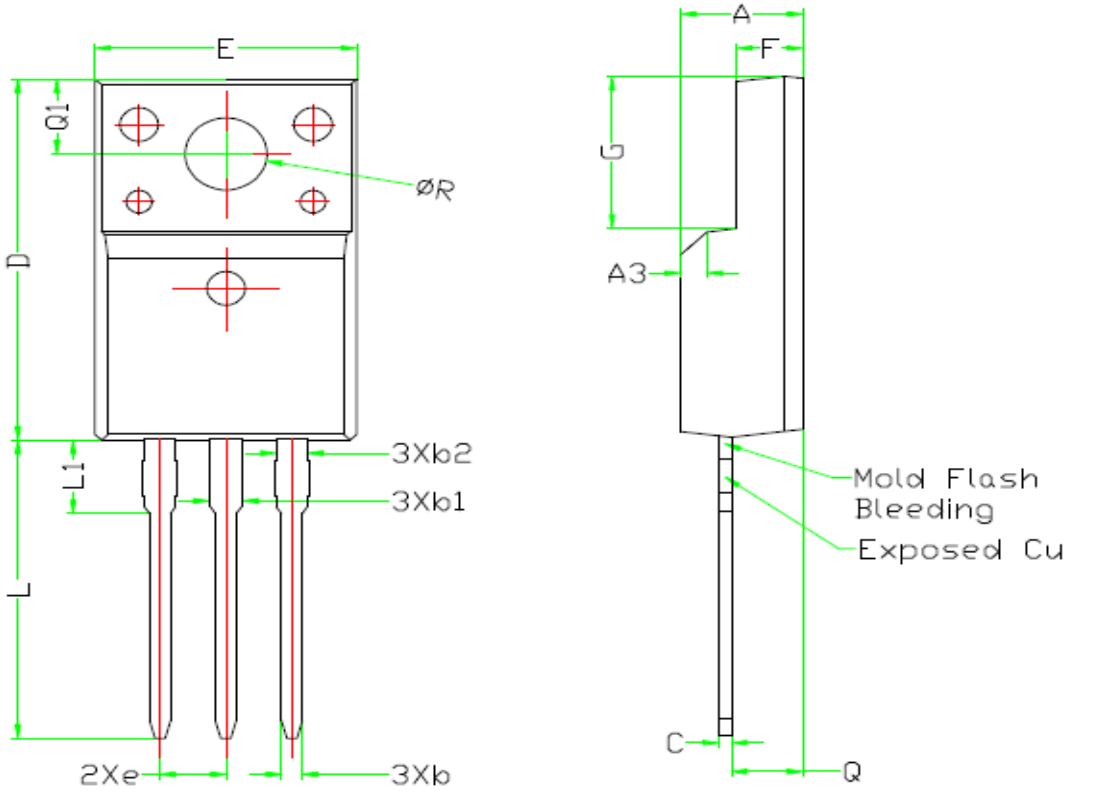


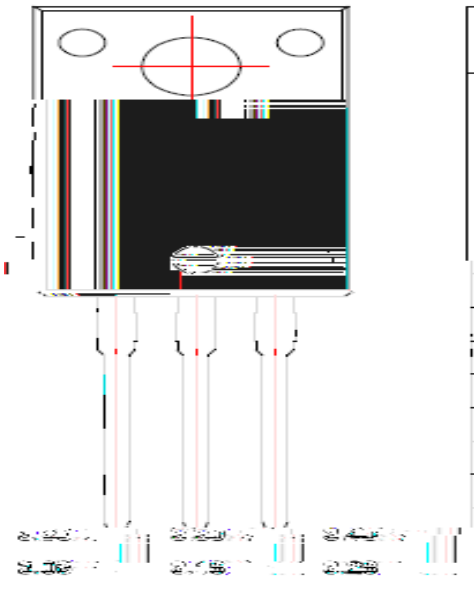
Diode Recovery Test



Package Outline

TO-22F, 3 leads





SYMBOL	DIMENSIONS		
	Min.	Nom.	Max.
A	4.60	4.70	4.80
b	0.72	0.83	0.91
b2	1.20	1.30	1.47
b3	1.10	1.20	1.30
c	0.48	0.50	0.63
D	15.60	15.67	15.87
e		2.54	
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85

BOTTOM VIEW

Note:

1. **All Dimension Are In mm.**
2. **Package Body Sizes Exclude**